

Horizontal Deflection Transistors

TELEFUNKEN electronic provides horizontal deflection transistors in both the high voltage TO 3 (large eyelet) hermetic package and in the high voltage epoxy package. Our basic structures use the time-proven and reliable triple diffusion technique combined with either back bevel or glass passivation edge termination methods, depending on the specific types.

Beside their intended function, and because of their extended safe operating area capabilities, these devices are admirably suited for many medium power flyback converter designs, high voltage linear regulator, and current limiter circuits.

NPN-Horizontal Deflection Power Transistors

Type	Maximum ratings					Characteristics			f_T at I_C		Case: Dimensions see page 8
	P_{tot}	at T_{case}	I_{CAV}	V_{CEO}	V_{CESM}	V_{CEsat} at I_C and I_{FE}					
	W	°C	A	V	V	V	A		MHz	mA	
BU 204	10.0	≤90	2.5	600	1300	≤5	2.0	2.0	7.5	100	Black/ White Colour Fig. 6
BU 205	10.0	≤90	2.5	700	1500	≤5	2.0	2.0	7.5	100	
BU 206	10.0	≤90	2.5	800	1700	≤5	2.0	1.8	7.5	100	
BU 225	32	≤25	1.5	800	2200	≤10	1.5	1.5	5.0	100	
BU 226	32	≤25	1.5	800	2000	≤10	1.5	1.5	5.0	100	
BU 207	12.5	≤90	5.0	600	1300	≤5	4.5	2.3	7.0	100	
BU 208	12.5	≤90	5.0	700	1500	≤5	4.5	2.3	7.0	100	
BU 208 A	12.5	≤90	5.0	700	1500	≤1	4.5	2.3	7.0	100	
BU 208 D ¹⁾	12.5	≤90	5.0	700	1500	-	-	-	7.0	100	
BU 209	12.5	≤90	5.0	800	1700	≤5	3.0	2.3	7.0	100	
S 518 T	12.5	≤90	5.0	700	1500	≤2	3.2	4	7.0	100	
S 630 T	12.5	≤90	5.0	800	1400	≤2	3.0	4	7.0	100	
BU 705	75	25	2.5	700	1500	≤5	2.0	2.2	7.0	100	B/W
BU 508	125	25	8.0	700	1500	≤5	4.5	2.25	7.0	100	Colour
BU 508 A	125	25	8.0	700	1500	≤1	4.5	2.25	7.0	100	
BU 508 D ¹⁾	125	25	8.0	700	1500	≤1	4.5	2.25	7.0	100	
BU 902	75	25	8.0	480	1100	≤5	4.0	5.5	7.0	100	Black/ White Fig. 8
BU 903	125	25	8.0	550	1350	≤2	3.2	5.0	7.0	100	
BU 908	125	25	8.0	700	1500	≤2	3.2	4.0	7.0	100	

Remarks:¹⁾ with integrated inverse diode